SamHop Microelectronics Corp.

STS3623

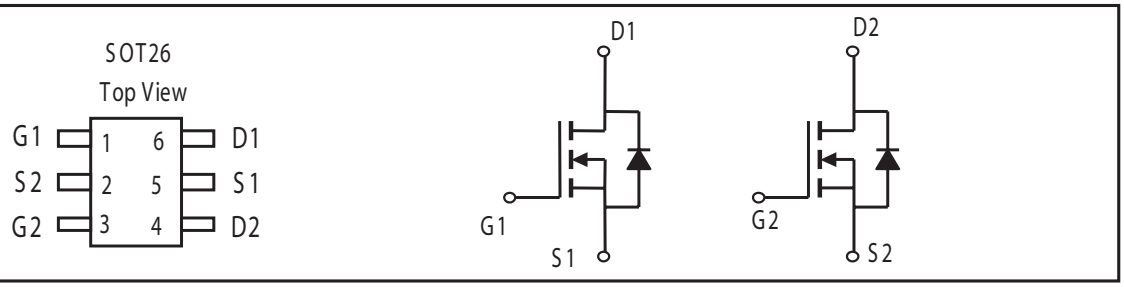
Jun, 09 2006

Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
30V	4A	50 @ V_{GS} = 10V 65 @ V_{GS} = 4.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- SOT-26 package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous @ T_J=25°C	I_D	4	A
-Pulsed [b]	I_{DM}	16	A
Drain-Source Diode Forward Current	I_S	1.25	A
Maximum Power Dissipation [a]	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	R_{thJA}	100	°C/W

STS3623

ELECTRICAL CHARACTERISTICS (T_A =25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V, V_{GS}=0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=± 20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3A		40	50	m-ohm
		V_{GS}=4.5V, I_D=2A		50	65	m-ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS}=5V, V_{GS}=4.5V	10			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=3A		7		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS}=15V, V_{GS}=0V f=1.0MHz		280		pF
Output Capacitance	C_{OSS}			70		pF
Reverse Transfer Capacitance	C_{RSS}			38		pF
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=15V, I_D=1A, V_{GS}=10V, R_{GEN}=6 ohm		6		ns
Rise Time	t_r			5		ns
Turn-Off Delay Time	$t_{D(OFF)}$			18		ns
Fall Time	t_f			6		ns
Total Gate Charge	Q_g	V_{DS}=15V, I_D=3A, V_{GS}=10V		5.9		nC
Gate-Source Charge	Q_{gs}			0.7		nC
Gate-Drain Charge	Q_{gd}			1.4		nC

STS3623

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ[c]	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [b]						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =1.25A		0.81	1.15	V

Notes

a.Surface Mounted on FR4 Board, t≤10sec.
b.Pulse Test:Pulse Width≤ 300us, Duty Cycle≤ 2%.
c.Guaranteed by design, not subject to production testing.

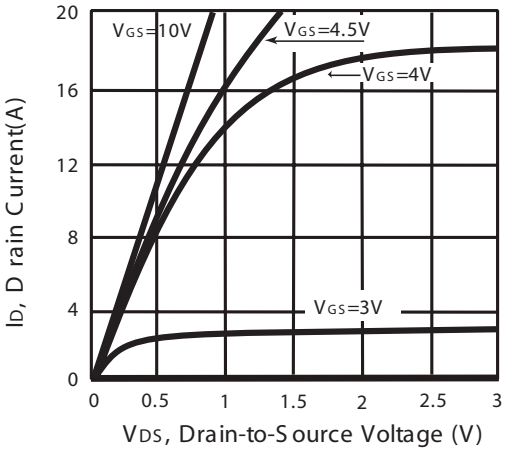


Figure 1. Output Characteristics

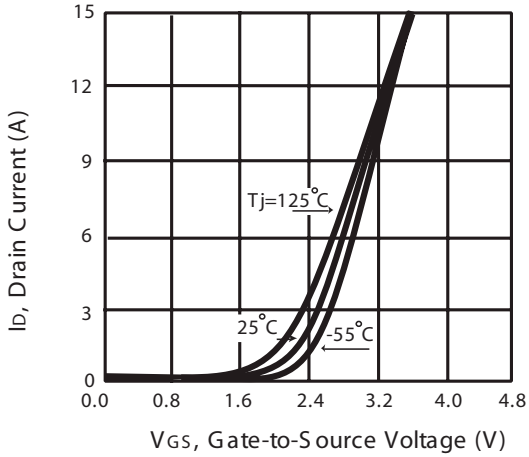


Figure 2. Transfer Characteristics

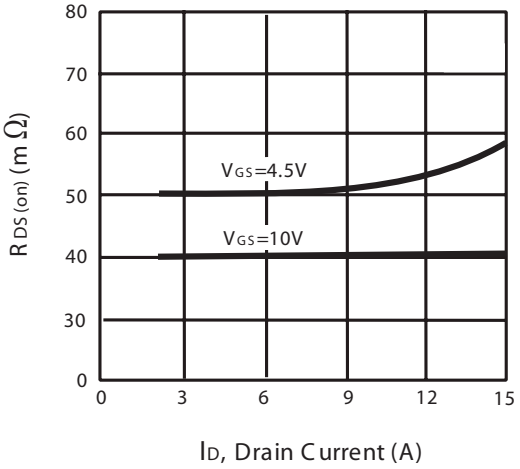


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

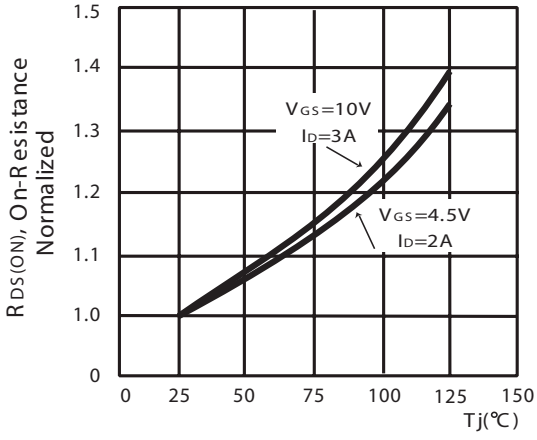


Figure 4. On-Resistance Variation with Temperature

STS3623

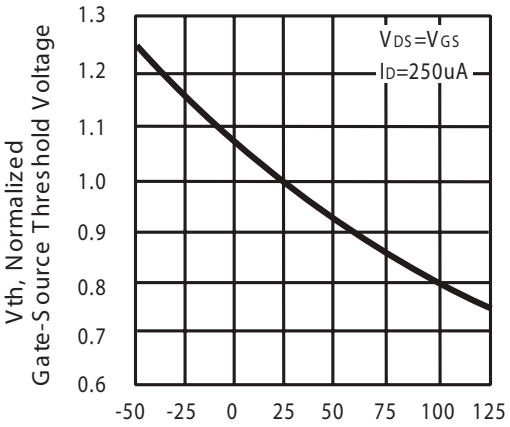


Figure 5. Gate Threshold Variation with Temperature

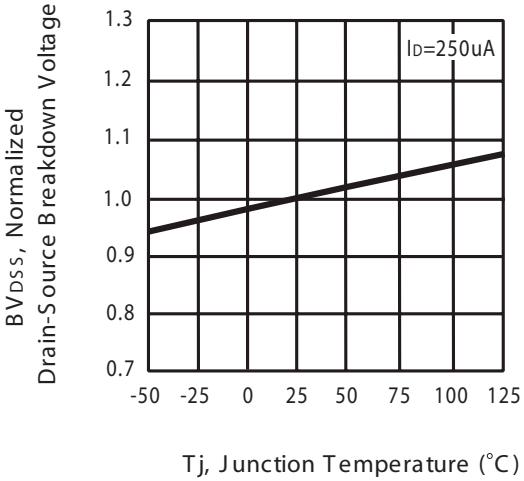


Figure 6. Breakdown Voltage Variation with Temperature

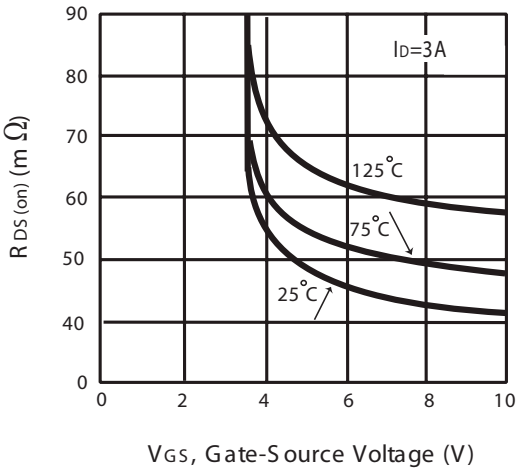


Figure 7. On-Resistance vs. Gate-Source Voltage

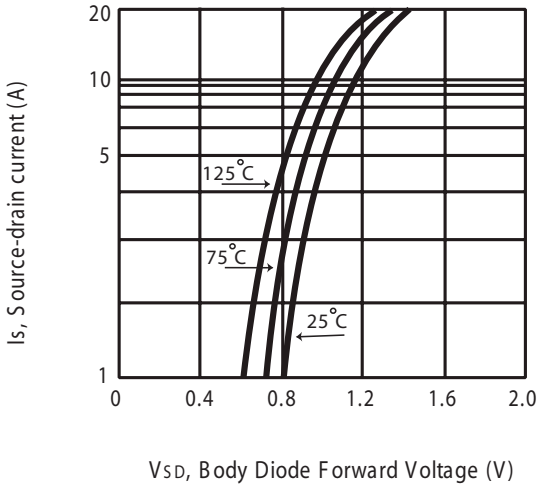


Figure 8. Body Diode Forward Voltage Variation with Source Current

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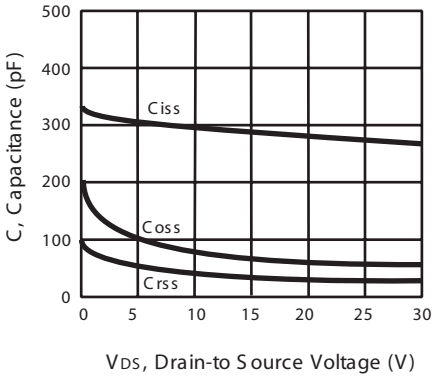


Figure 9. Capacitance

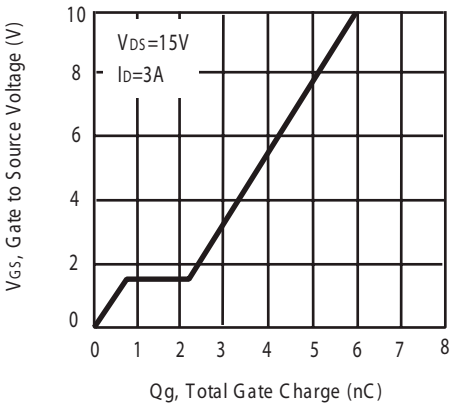


Figure 10. Gate Charge

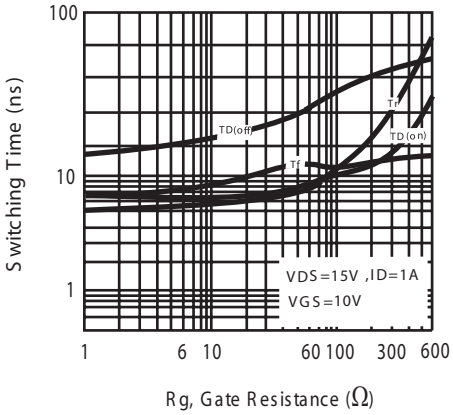


Figure 11.switching characteristics

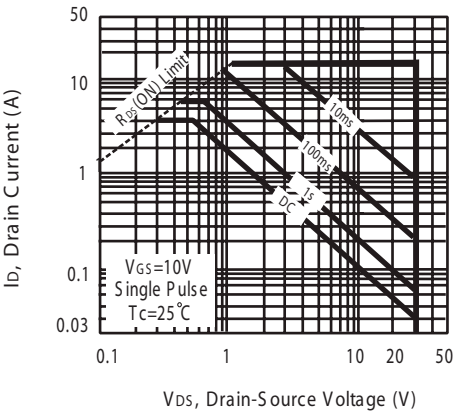


Figure 12. Maximum Safe Operating Area

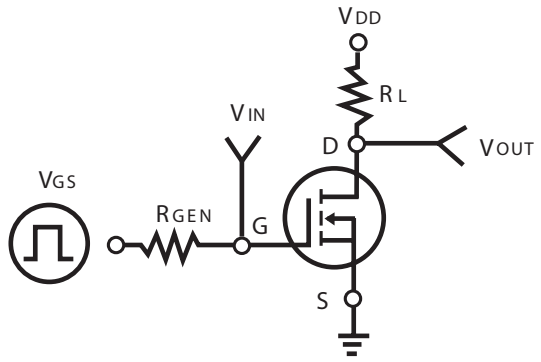


Figure 11. Switching Test Circuit

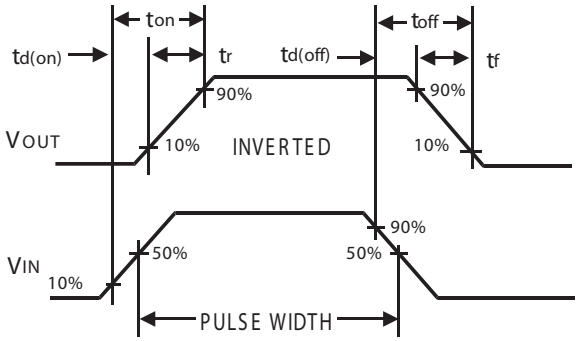
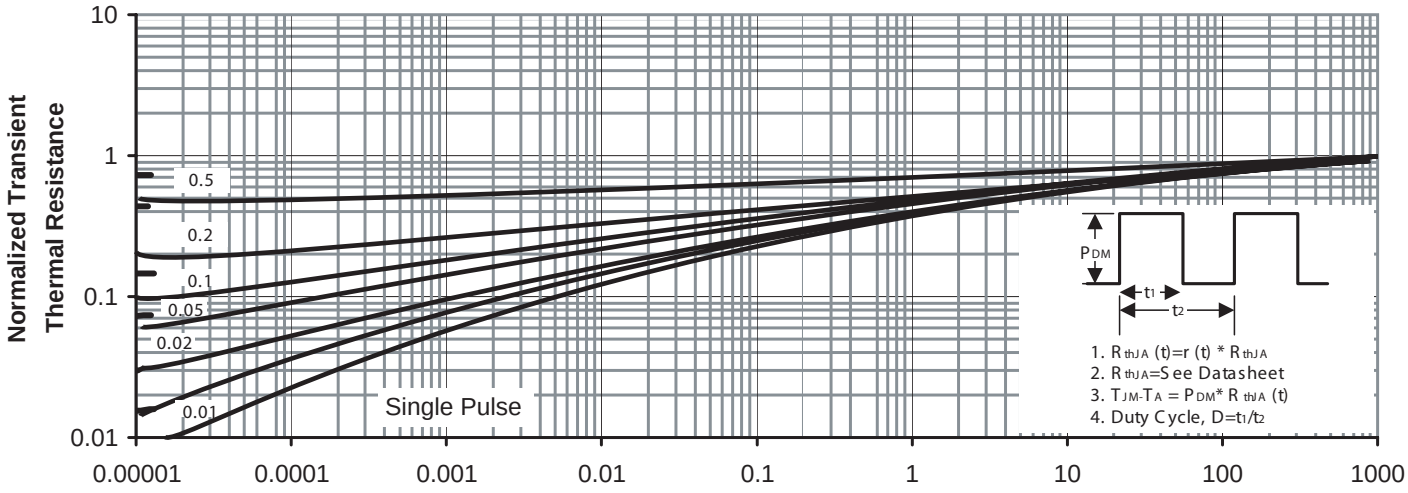


Figure 12. Switching Waveforms

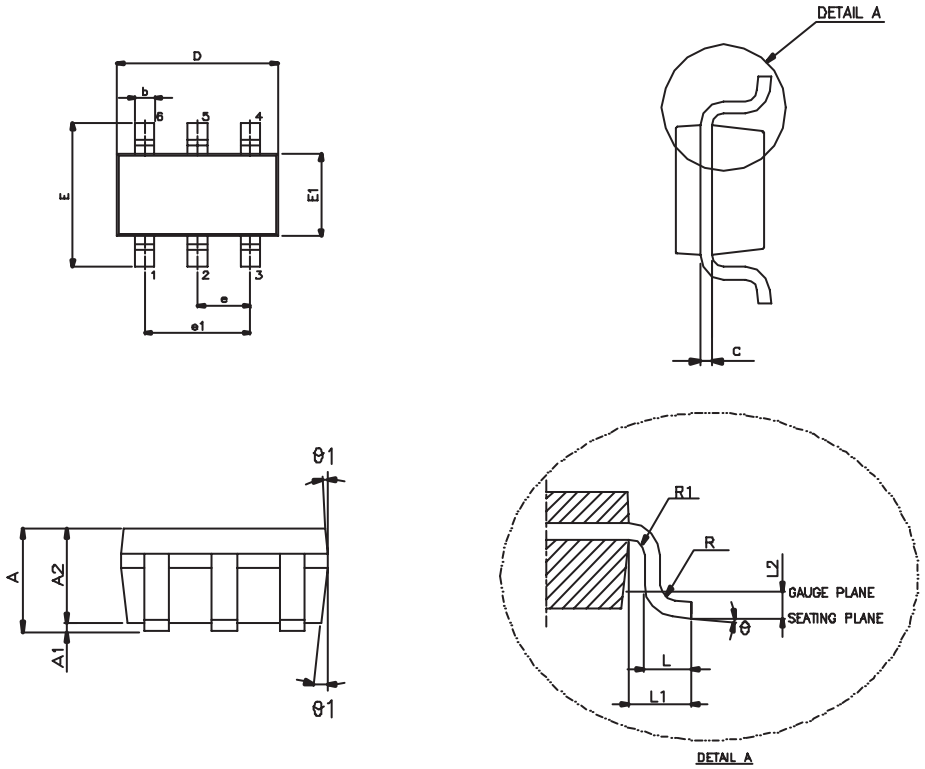


Normalized Thermal Transient Impedance Curve

STS3623

PACKAGE OUTLINE DIMENSIONS

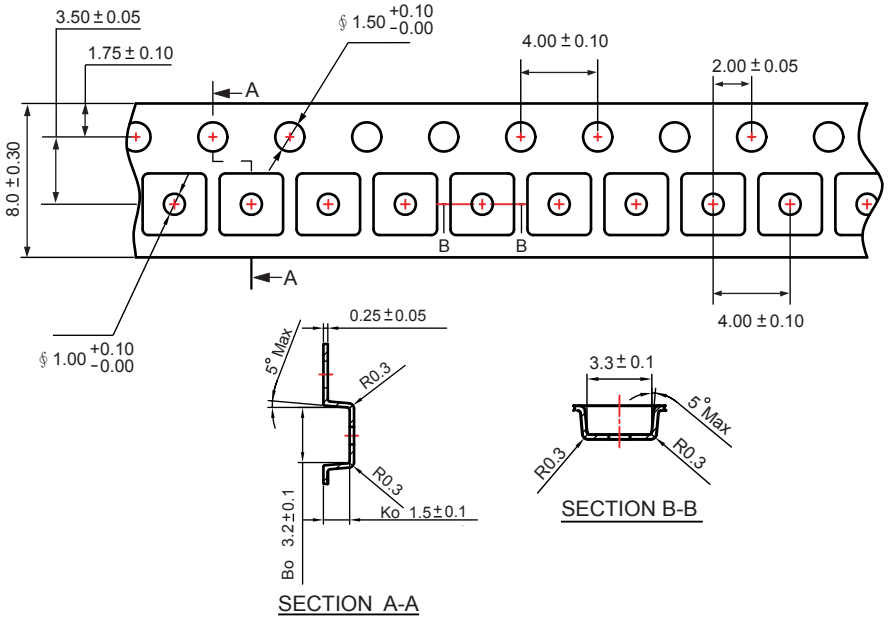
SOT26



SYMBOL	MIN.	NOM.	MAX.
A	–	–	1.45
A1	–	–	0.15
A2	0.90	1.15	1.30
b	0.30	–	0.50
c	0.08	–	0.22
D	2.90 BSC.		
E	2.80 BSC.		
E1	1.60 BSC.		
e	0.95 BSC		
e1	1.90 BSC.		
L	0.30	0.45	0.60
L1	0.60 REF.		
L2	0.25 BSC.		
R	0.10	–	–
R1	0.10	–	0.25
θ	0°	4°	8°
θ1	5°	10°	15°

SOT 26 Tape and Reel Data

SOT 26 Carrier Tape



SOT 26 Reel

